优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码　　企业QQ二维码

Features

- BV_{CEO} > -20V
- I_C = -5A Continuous Current
- Low Saturation Voltage $V_{CE(sat)}$ < -0.5V @ -50mA
- P_D = 2.4W Power Dissipation
- R_{sat} = 39mΩ for a Low Equivalent On-Resistance
- Complementary part number NK-ZXTN25020DZ

Mechanical Data

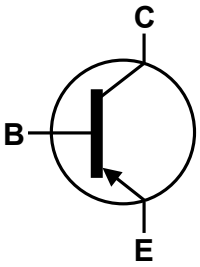
- Case: SOT89
- Case Material: Molded Plastic. “Green” Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.05 grams (Approximate)

Application

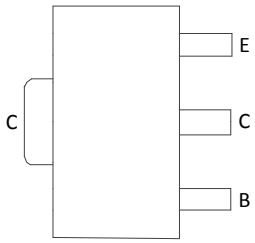
- DC-DC converters
- Load switch
- Motor drive
- Disconnect switch
- MOSFET and IGBT gate drive

SOT89

Top View



Device Symbol



Top View
Pin Out

Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

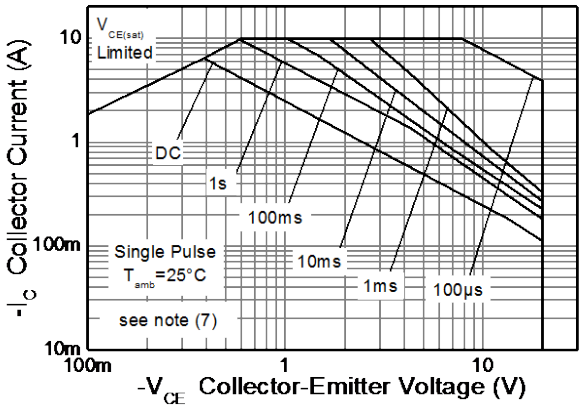
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-25	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Collector voltage (reverse blocking)	V_{ECO}	-4	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-5	A
Base current	I_B	-1	A
Peak Pulse Current (Single pulse)	I_{CM}	-10	A

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

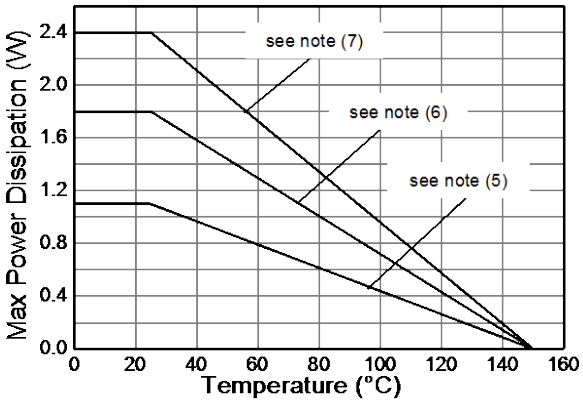
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	P_D	1.1 8.8	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	P_D	1.8 14.4	W mW/°C
Power Dissipation (Note 7) Linear Derating Factor	P_D	2.4 19.2	W mW/°C
Power Dissipation (Note 8) Linear Derating Factor	P_D	4.46 35.7	W mW/°C
Power Dissipation (Note 9) Linear Derating Factor	P_D	15.7 126	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	117	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	68	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	51	°C/W
Thermal Resistance, Junction to Ambient (Note 8)	$R_{\theta JA}$	28	°C/W
Thermal Resistance, Junction to Case (Note 9)	$R_{\theta JC}$	7.95	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes:
5. For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.
6. Same as note (5), except the device is mounted on 25mm x 25mm x 0.6mm single sided 1oz weight copper.
7. Same as note (5), except the device is mounted on 50mm x 50mm x 0.6mm single sided 1oz weight copper.
8. Same as note (5), except the device is measured at t<5 seconds
9. Junction to case (collector tab). Typical.

Thermal Characteristics and Derating Information

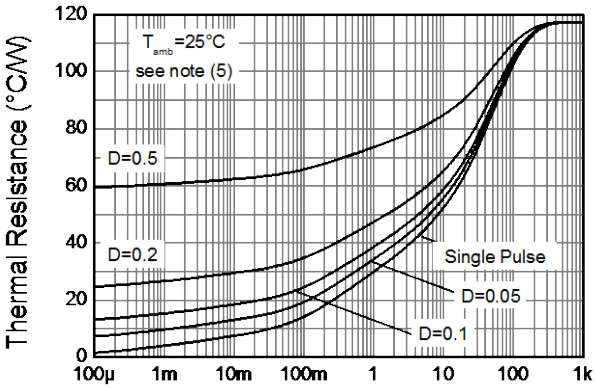


Safe Operating Area

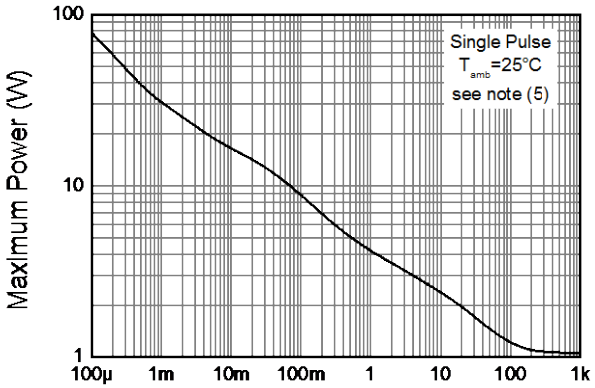


Derating Curve

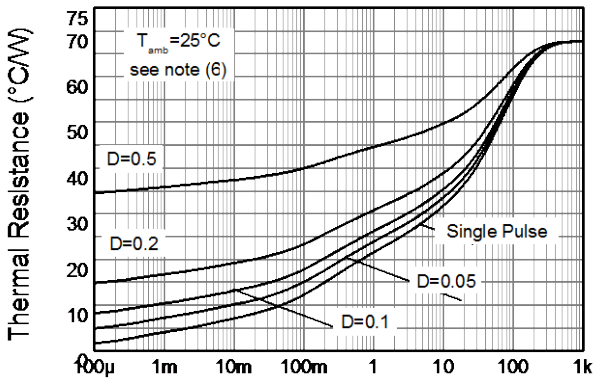
Thermal Characteristics and Derating Information



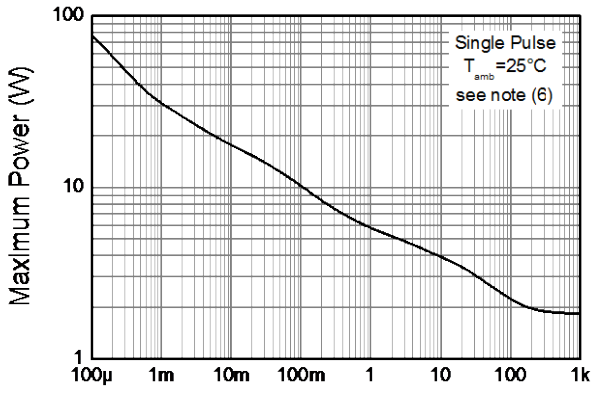
Transient Thermal Impedance



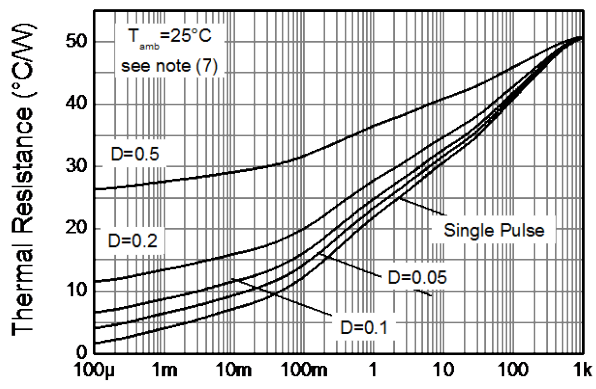
Pulse Power Dissipation



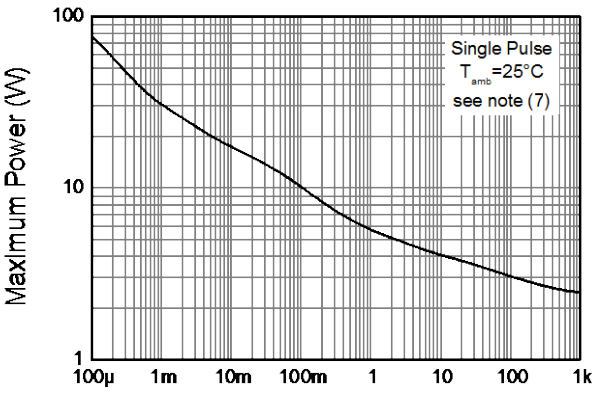
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



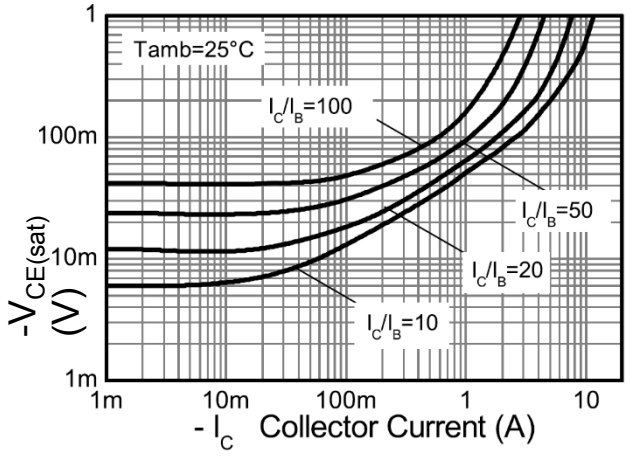
Pulse Power Dissipation

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

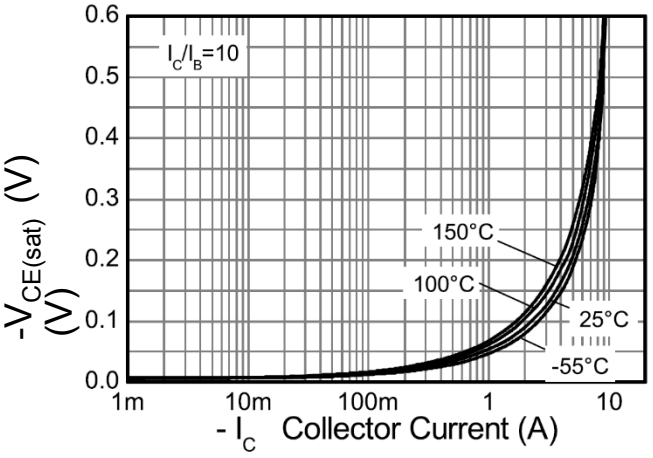
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-25	-55	—	V	I_C = -100μA
Collector- Emitter Breakdown Voltage (Note 10)	BV_{CEO}	-20	-45	—	V	I_C = -10mA
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	-4	-8.5	—	V	I_E = -100μA, R_{BC} ≤ 1kΩ or 0.25V > V_{BE} > -0.25V
Emitter-Collector Breakdown Voltage	BV_{ECO}	-4	-8.5	—	V	I_E = -100μA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.3	—	V	I_E = -100μA
Collector Cut-Off Current	I_{CBO}	—	-1 —	-50 -0.5	nA μA	V_{CB} = -25V V_{CB} = -25V, T_A = +100°C
Emitter Cut-Off Current	I_{EBO}	—	-1	-50	nA	V_{EB} = -5.6V
Collector-Emitter Saturation Voltage (Note 10)	$V_{CE(sat)}$	—	-50 -150 -185 -195	-65 -215 -245 -265	mV	I_C = -1A, I_B = -100mA I_C = -1A, I_B = -10mA I_C = -2A, I_B = -40mA I_C = -5A, I_B = -500mA
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(sat)}$	—	-1010	-1100	mV	I_C = -5A, I_B = -500mA
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(on)}$	—	-870	-1000	mV	I_C = -5A, V_{CE} = -2V
DC current gain (Note 10)	h_{FE}	300 200 45 —	450 310 85 20	900 — — —	—	I_C = -10mA, V_{CE} = -2V I_C = -1A, V_{CE} = -2V I_C = -5A, V_{CE} = -2V I_C = -10A, V_{CE} = -2V
Transitional frequency	f_T	—	290	—	MHz	I_C = -50mA, V_{CE} = -10V, f = 100MHz
Input Capacitance	Ci_{bo}	—	21	—	pF	V_{EB} = -0.5V, f = 1MHz
Output Capacitance	C_{obo}	—	157	—	pF	V_{CB} = -10V, f = 1MHz
Delay time	t_d	—	14.2	—	ns	I_C = -1A, V_{CC} = -10V, I_{B1} =-I_{B2} = -50mA
Rise time	t_r		16.3			
Storage time	t_s		186			
Fall time	t_f		32.7			

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

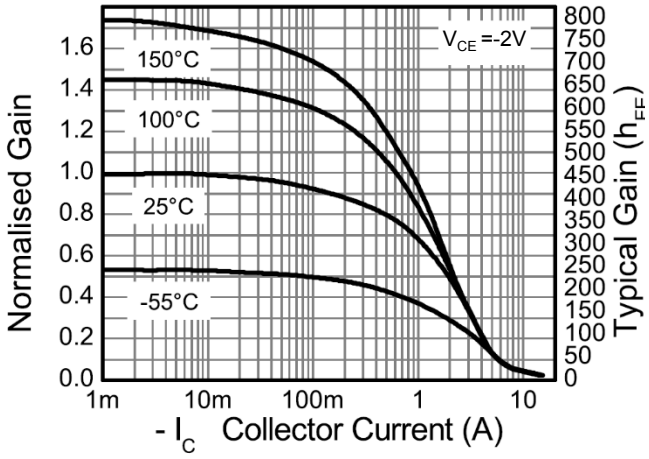
Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)



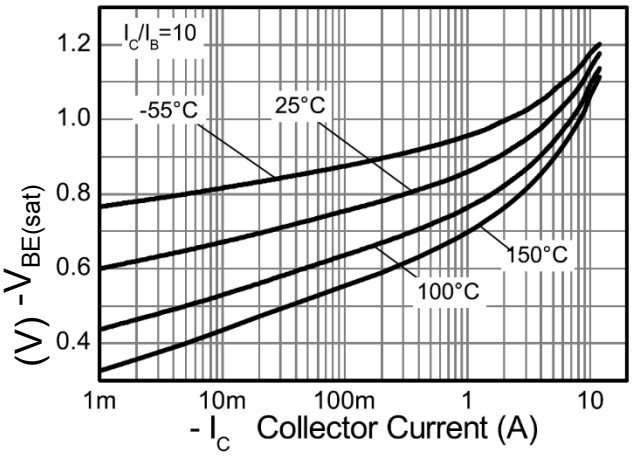
$V_{CE(sat)}$ v I_C



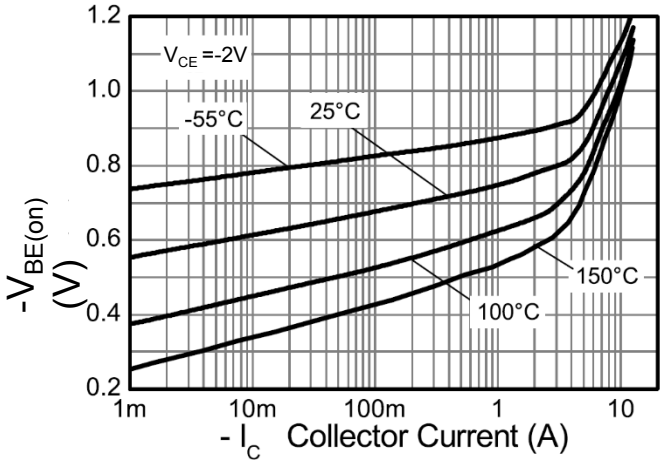
$V_{CE(sat)}$ v I_C



h_{FE} v I_C



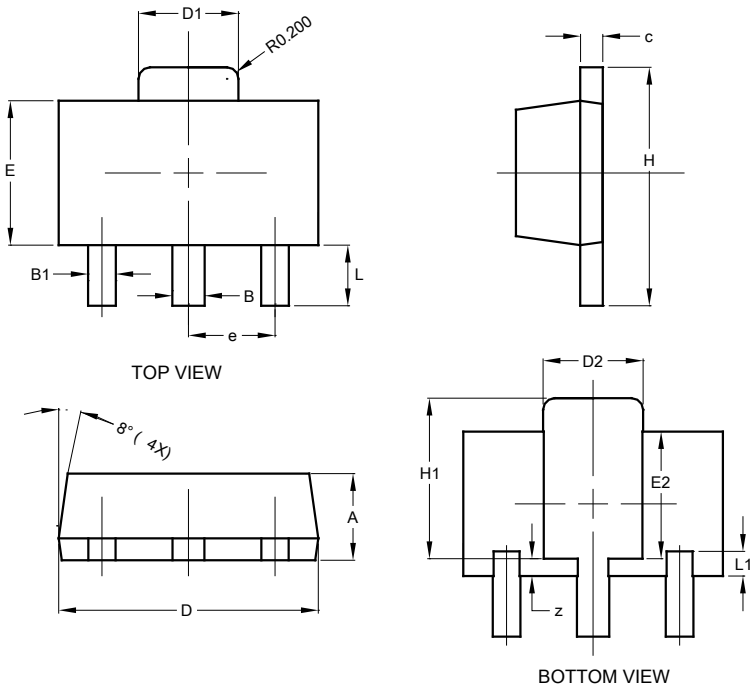
$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C

Package Outline Dimensions

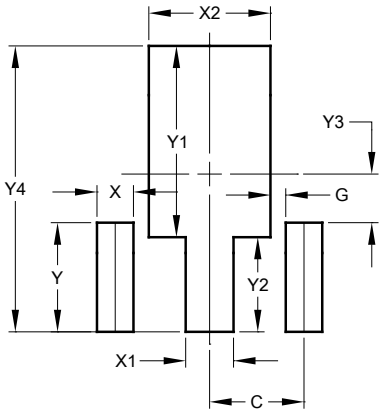
SOT89



SOT89			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530